

SCHOTTKY-BARRIER DIODES

Silicon epitaxial Schottky Barrier diodes with an integrated p-n junction protection ring in a microminiature SOT-23 envelope intended for surface mounting.

The diodes feature an especially low forward voltage.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max. 30 V
Forward current (DC)	I_F	max. 200 mA
Forward voltage at $I_F = 10$ mA	V_F	max. 400 mV
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA, $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	< 5 ns
Junction temperature	T_j	max. 125 °C

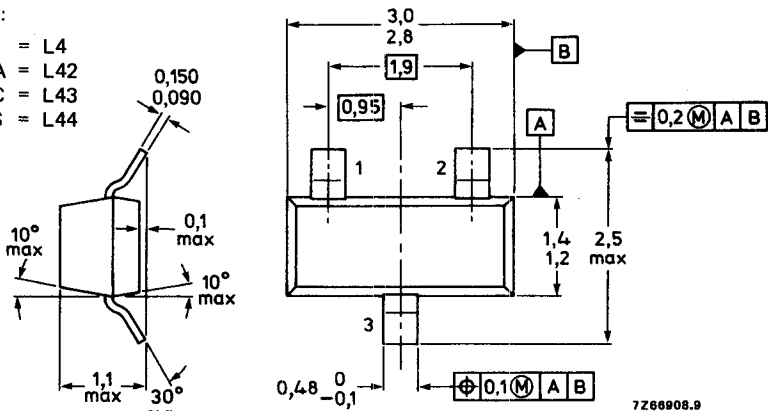
MECHANICAL DATA

Dimensions in mm

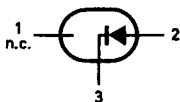
Fig.1 SOT-23.

Marking:

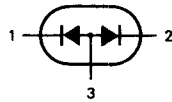
- BAT54 = L4
- BAT54A = L42
- BAT54C = L43
- BAT54S = L44



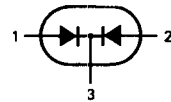
TOP VIEW



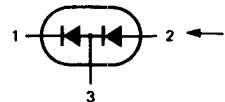
BAT54



BAT54A



BAT54C



BAT54S

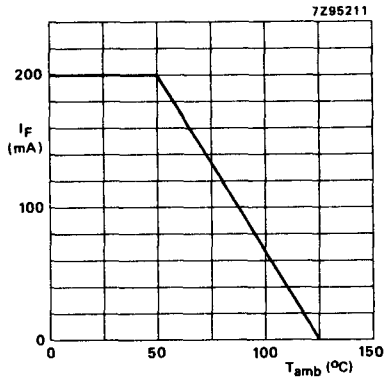


Fig. 2 Derating curve maximum ambient temperature.